광원 적용을 위한 DLC합성

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Fabrication Technology of DLC for New Light Source

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Abstract - Carbon films was grown on Si substrates using the method of electrolysis for methanol liquid. Deposition parameters for the growth of the carbon films were current density for the electrolysis, methanol liquid temperature and electrode spacing between anode and cathode. We examined electrical resistance and the surface morphology of carbon films formed under various conditions specified by deposition parameters. It was clarified that the high electrical resistance carbon films with smooth surface morphology are grown when a distance between the electrodes was relatively wider. We found that the electrical resistance in the films was independent of both current density and methanol liquid temperature for electrolysis. The temperature dependence of the electrical resistance in the low resistance carbon films was different from one obtained in graphite.

1. 서 론

Carbon was known to be a typical high temperature semiconductor, very inert to chemical substrances, and a number of attemps have been made to fabricate both passive and active electronic devices using diamond[1]. The thin films of diamond like carbon have recently attracted much interest for their potential use as hard, wear resistant films, and optical coatings. The method s known for depositing carbon films, such as pulsed laser deposition[2], and ion beam deposition[3], were all vapor deposition techniques. Using these techniques, high quality films and rapid growth rate have been achieved. There was experimental evidence that most materials which can be deposited from the vapor phase can also be deposited in liquid phase using electroplating techniques and vice versa[4]. Suzuki et al [5]. Recently made an attempt to deposit carbon phase in the films by electrolysis of a water ethylene glycol solution. Graphitic carbon had been obtained according to their Raman spectra. Nevertheless, ethylene glycol was a viscous solution, which will cause some difficulty in cleaning substrates after deposition. Since carbon films synthesized in the liquid phase has significant scientific and technological implications, it is worth pursuing research with other electrolysis. In this work, a film deposition was attempted in methanol solution by the techniques of electrolysis. Methanol is selected because its polarizability and conductivity are stronger than those of ethanol, and the structure of methanol is even closer to that of carbon.

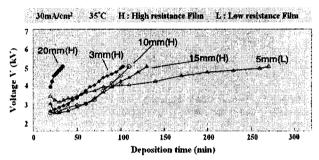
2. 실험 방법

Analytically pure methanol (99.5%) was used as electrolyte. A s ilicon (100) substrate with a size of $15\times20\times0.3\text{mm}^3$ was mounted on the negative electrode. Before deposition the substrate were in the mixture of dilute HNO3-HF solution for a few minutes and then cleaned by ultrasonic treatment. The distance between the substrate and positive electrode was set to 10mm. The potential applied to the substrate could be changed from 0 to 5000 V under a constant temperature. The deposited films were examined by scanning electron microscopy (SEM).

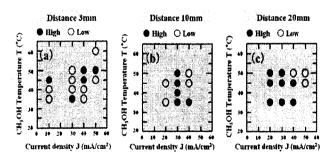
3. 결과 및 고찰

Fig.1 is the D.C. voltage change at a constant current density of 30mA/cm^2 with distance between Si and graphite electrode. As shown in Fig.2, in which the resistance more than 20 Macmarked H in figure) were observed at 35°C constant solution temperature

at each electrode distance such as 3, 5, 10, 15 and 20 mm respectively. Low resistance marked L in figure means about 10k $^{\circ}$ - 100k varies. Since the current density was kept constantly during the measurement of resistance, the voltage increased with deposition time. One of interesting points in Fig.1, the tendency of voltage increment depends on the resistance. For example, low resistance with 5 mm electrode distance shows moderate increment of the voltage, whereas, high resistance with different electrode distance like 3, 10, 15 and 20 mm shows stiffly increment of the voltage. The moderate increment of the voltage means the deposition of carbon film with low resistance on silicon substrate. The high increment of the resistance results from the dopants of the carbon film with high resistance on the silicon substrate. From the Fig.1, its voltage change during electrolysis deposition considered as one of the parameters to evaluate the final deposit.



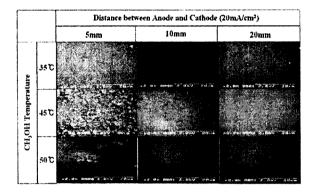
<그림 1> Electrode distance and voltage change with deposition time.



<그림 2> Electrical resistance change with current density and solution temperature.

Fig.2 is the resistance change with current density and solution temperature at a constant electrode distance. Solid and open circl es in the Fig.2 are carbon film with high resistance and that with low resistance, respectively. As shown in Fig.3, the carbon film with low resistance was well deposited than the carbon film with high resistance. As the electrode of distance was broad away from 10 to 20 mm, the carbon film with high resistance was well formed. Especially, the carbon film with highresistance was well formed at the vary of current density, 20-40 mA/cm² at 30-50°t. The surface of the carbon film is usually smoother than that of diamond film. The smoothness is one of important factor

for the application of electronic device. The smoothnessinfluence t he effect of electric field emission, for the electronic field emitter, it is important to enhance the smoothness. In this study, methan ol, CH3OH, was electrolysis decomposed with electrode in distanc e. Fig.3 is surface morphology is observed by scanning electron microscopy. As shown in Fig.3, rough carbon surface was observ ed at the current density of 20 mA/cm² and a constant electrode distance of 5 mm. The surface roughness was decreased while in creasing electrode distance from 10 to 20 mm. This means that t he surface roughness was increased with decreasing electrode dis tance, resultantly,the carbon film with low resistance was formed. However, the surface roughness was decreased with increasing el ectrode distance, resultantly, the carbon film with high resistance was formed. In use of narrow electrode distance less than micro scale with high current density, electric spark was occurred, that increases the solution temperature. The high solution temperature by the electric spark changes the electrolysis deposition condition which results in decreasing surface smoothness and forming the carbon film with low resistance.



<크림 3> Surface morphology change of carbon films with electrode distance formed at 20mA/cm².

4. 결 뿐

Carbon films were electrolysis on Si substrates in methanol solution. The carbon films with high electrical resistance and smooth surface were formed when the distance between the electrodes was relatively wider. Surface roughness was decreased with increasing electrode distance, which tended to form the carbon film with high resistance. The electrical resistance of the films was independent of both current density and methanol liquid temperature.

감사의 글

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[참 고 문 헌]

- H. Maeda, Y. Tanaka, M. Hukutomi, "Bi-based High Tc Superconductors" Jpn. J. Appl. Phys., Vol. 27, No. 2, p.209, 1988.
- [2] J. Yang, D. Shi, X. Wang, A. Liu, and G.Yuan, "Fabrication of YBCO coated conductors using magnetron sputtering", Physica C, Vol. 341, p.2499, 2000.